Dominik Metzler

List of Publications by Year
in descending order

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14 papers	514 citations	933447 10 h-index	1125743 13 g-index
14 all docs	14 docs citations	14 times ranked	311 citing authors

#	Article	IF	Citations
1	Fluorocarbon assisted atomic layer etching of SiO2 using cyclic Ar/C4F8 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, .	2.1	161
2	Fluorocarbon based atomic layer etching of Si3N4 and etching selectivity of SiO2 over Si3N4. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	75
3	Fluorocarbon assisted atomic layer etching of SiO2 and Si using cyclic Ar/C4F8 and Ar/CHF3 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	74
4	Achieving ultrahigh etching selectivity of SiO2 over Si3N4 and Si in atomic layer etching by exploiting chemistry of complex hydrofluorocarbon precursors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	40
5	Characterizing fluorocarbon assisted atomic layer etching of Si using cyclic Ar/C4F8 and Ar/CHF3 plasma. Journal of Chemical Physics, 2017, 146, 052801.	3.0	35
6	Feasibility of atomic layer etching of polymer material based on sequential O2 exposure and Ar low-pressure plasma-etching. Applied Physics Letters, 2013, 102, .	3.3	31
7	Effect of the chamber wall on fluorocarbon-assisted atomic layer etching of SiO2 using cyclic Ar/C4F8 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 040603.	2.1	24
8	Investigation of thin oxide layer removal from Si substrates using an SiO₂atomic layer etching approach: the importance of the reactivity of the substrate. Journal Physics D: Applied Physics, 2017, 50, 254006.	2.8	24
9	Application of cyclic fluorocarbon/argon discharges to device patterning. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	17
10	Selective atomic layer etching of HfO2 over silicon by precursor and substrate-dependent selective deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	16
11	Formation of nanometer-thick delaminated amorphous carbon layer by two-step plasma processing of methacrylate-based polymer. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	1.2	8
12	He plasma pretreatment of organic masking materials for performance improvement during pattern transfer by plasma etching. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 041604.	1.2	5
13	Significance of plasma-photoresist interactions for atomic layer etching processes with extreme ultraviolet photoresist. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	4
14	Controlling Asymmetric Photoresist Feature Dimensions during Plasma-Assisted Shrink. Plasma Processes and Polymers, 2014, 11, 714-720.	3.0	0